

Notice of References Cited		Application No. <b>09-545,549</b>		Applicant(s) <b>Hirano et. al.</b>	
		Examiner <b>George Goudreau</b>		Group Art Unit <b>1763</b>	
Pag <b>1</b> of <b>1</b>					
U.S. PATENT DOCUMENTS					
☆	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
A	<b>6,413,833</b>	<b>7-2-02'</b>	<b>Yamamoto</b>	<b>438</b>	<b>398</b>
B	<b>6,232,628</b>	<b>5-15-01'</b>	<b>Shirosaki et. al.</b>	<b>257</b>	<b>306</b>
C	<b>6,368,913</b>	<b>4-9-02'</b>	<b>Yamamoto</b>	<b>438</b>	<b>255</b>
D					
E					
F					
G					
H					
I					
J					
K					
L					
M					
FOREIGN PATENT DOCUMENTS					
☆	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS
N	<b>11-238,863</b>	<b>8-31-99'</b>	<b>Japan</b>	<b>Son</b>	
O	<b>09-036,320</b>	<b>2-7-97'</b>		<b>Yamagata</b>	
P	<b>11-097,641</b>	<b>4-9-99'</b>	↓	<b>Takayuki</b>	
Q					
R					
S					
T					
NON-PATENT DOCUMENTS					
☆	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)				DATE
U	<b>"A New Cylindrical Capacitor Using Hemispherical Grained Si (HSG-Si) For 256Mb DRAMS"; Watanabe et. al.; International Electron Devices Meeting; 1992'; pp 259-262</b>				
V					
W					
X					

\* A copy of this reference is not being furnished with this Office action.  
(See Manual of Patent Examining Procedure, Section 707.05(a).)